

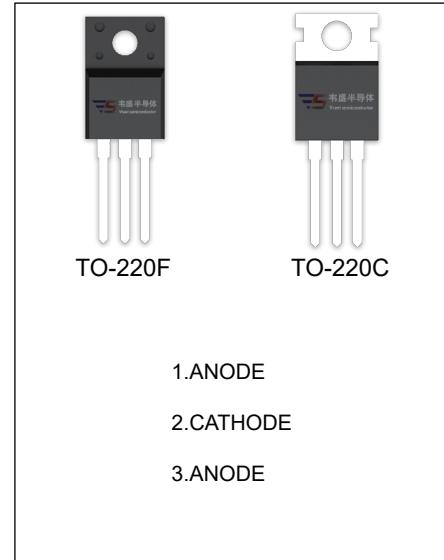
SBD20150TA、SBDF20150TA SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

I_o	20A
V_{RRM}	150 V
T_j	150°C
V_{F(typ)}	0.74V (@Tj=125°C)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



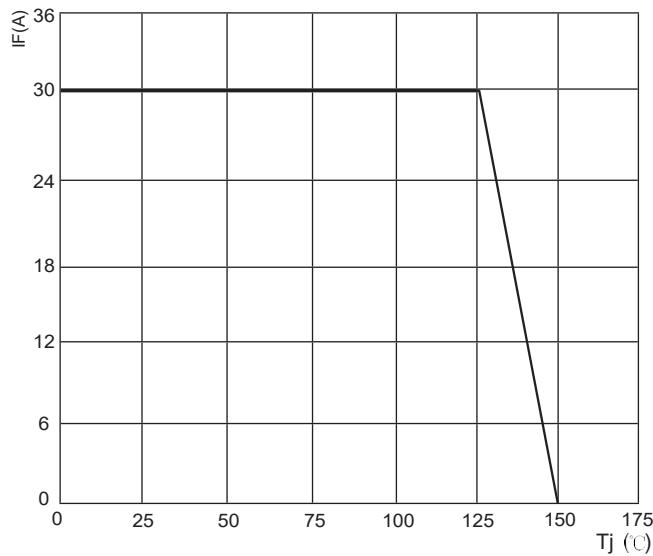
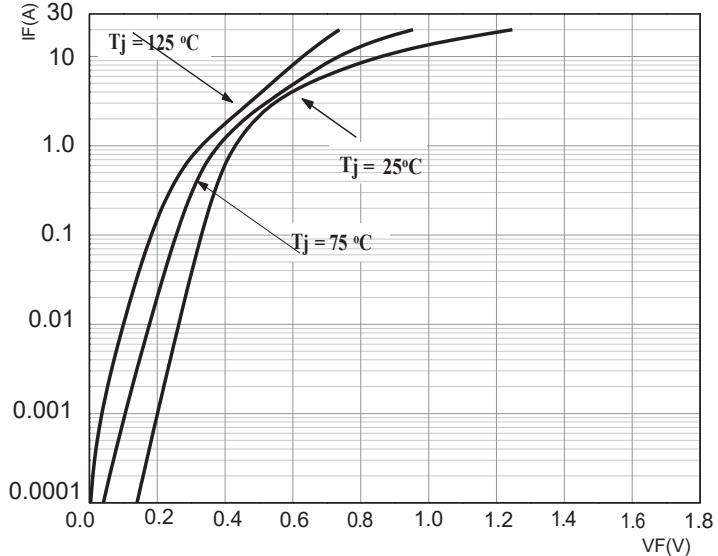
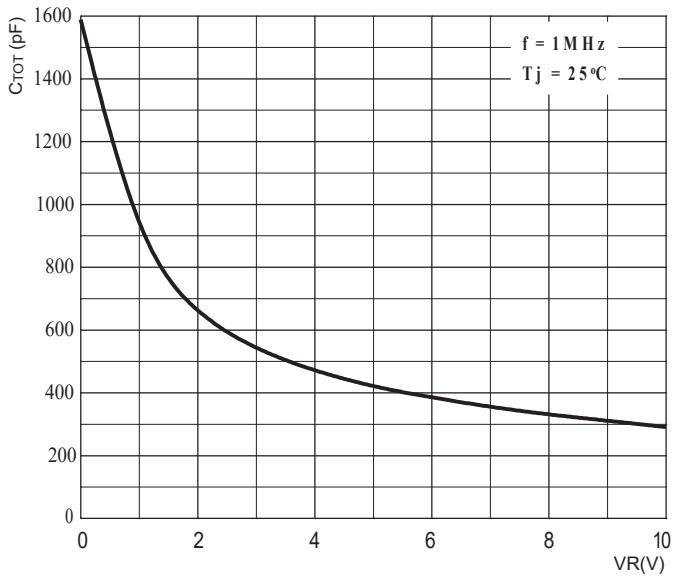
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	SBD		Unit
		20150TA	F20150TA	
V_{RRM}	Peak repetitive reverse voltage			
V_{RWM}	Working peak reverse voltage		150	V
V_R	DC blocking voltage			
V_{R(RMS)}	RMS reverse voltage		105	V
I_o	Average rectified output current		20	A
I_{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)		200	A
R_{θJC}	Thermal resistance from junction to case , T _c =25°C	2.0	3.0	°C/W
R_{θJA}	Thermal resistance from junction to ambient		62.5	°C/W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse voltage	V_(BR)	I_R=0.1mA		150			V
Reverse current	I_R	V_R=150V	T_j=25°C		5.0	30	uA
			T_j=125°C		5.0		mA
Forward voltage	V_F	I_F=10A	T_j=25°C		0.84		V
			T_j=125°C		0.63		V
		I_F=20A	T_j=25°C		1.25	1.30	V
			T_j=125°C		0.74		V

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

FIG.1: FORWARD CURRENT DERATING CURVE

FIG.2: TYPICAL FORWARD CHARACTERISTICS

FIG.3: TOTAL CAPACITANCE DERATING CURVE

FIG.4: TYPICAL REVERSE CHARACTERISTICS
